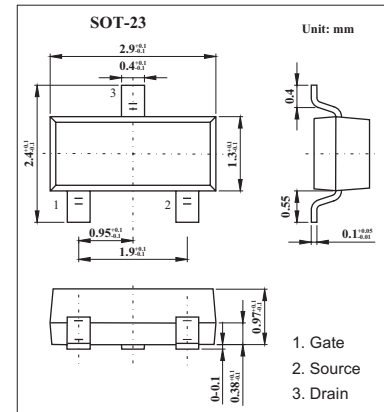
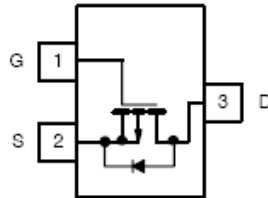


P-Channel 2.5-V (G-S) MOSFET

LSP01

■ Features

- RoH Lead (Pb)-Free Version is RoHS Compliant.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	5 sec	Steady State	Unit
Drain-Source Voltage	V_{DS}		-20	V
Gate-Source Voltage	V_{GS}		± 8	V
Continuous Drain Current ($T_J=150^\circ\text{C}$) *2 $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	I_D	-2.4 -1.9	-2.2 -1.8	A
Pulsed Drain Current *1	I_{DM}		-10	A
Continuous Source Current (diode conduction) *2	I_S	-0.72	-0.6	A
Power Dissipation *2 $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	P_D	0.9 0.57	0.7 0.45	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

* 1. Pulse width limited by maximum junction temperature.

* 2. Surface Mounted on FR4 Board, $t \leq 5$ sec.

■ Thermal Resistance Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient *1	R_{thJA}	120	145	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient *2		140	175	

* 1. Surface Mounted on FR4 Board, $t \leq 5$ sec.

* 2. Surface Mounted on FR4 Board.

LSP01

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.45		-0.95	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-6			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -2.5\text{ V}$	-3			
Drain-Source On-State Resistance *	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		0.08	0.1	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$		0.11	0.15	
Forward Transconductance *	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		6.5		S
Diode Forward Voltage *	V_{SD}	$I_S = -0.75\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		4.5	10	nC
Gate-Source Charge	Q_{gs}		0.7			
Gate-Drain Charge	Q_{gd}		1.1			
Input Capacitance	C_{iss}	$V_{DS} = -6\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$		375		pF
Output Capacitance	C_{oss}		95			
Reverse Transfer Capacitance	C_{rss}		65			
Turn-On Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\Omega, I_D = -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\Omega$		20	30	ns
	t_r			40	60	
Turn-Off Time	$t_{d(off)}$			30	45	
	t_f			20	30	

* Pulse test: $PW \leq 300\ \mu\text{s}$ duty cycle $\leq 2\%$.